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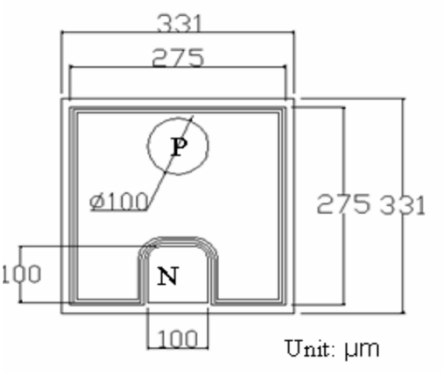
Product Data Sheet

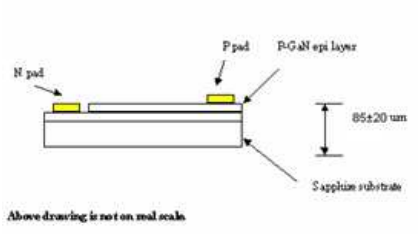
UV LED Chip EOLC-395-34 Rev. 03, 2017

Radiation	Type	Electrodes
ultraviolet (UV)	InGaN / sapphire	P + N up



Description

- Sustrate: Sapphire, epitaxial layer: GaN based material
- N bonding pad electrode: Au alloy
- P bonding pad electrode: Au alloy



Maximum Ratings

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward current (DC)		I_F			20	mA
Peak forward current	$t_p \leq 50$ µs, $t_p/T = ½$	I_{FM}			100	mA

Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=20 mA	V_F		3.5	3.8	V
Reverse current	V_R=5 V	I_R			1	µA
Peak wavelength	I_F=20 mA	λ_p	390	395	400	nm
FWHM	I_F=20 mA	$\Delta\lambda_{0.5}$		30		nm
Radiant power*	I_F=20 mA	Φ_e	4		5	mW

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire-bond side top

Art. No. 111 010

RoHS COMPLIANT Pb Pb-Free